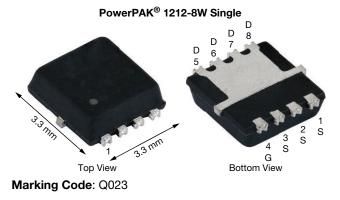
### SQS401ENW



**Vishay Siliconix** 

## Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-40				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.029				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.047				
I <sub>D</sub> (A)	-16				
Configuration	Single				
Package	PowerPAK 1212-8W				



#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified d
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

P-Channel MOSFET



RoHS COMPLIANT HALOGEN FREE

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	-40	 		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	I	-16		
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-16		
Continuous Source Current (Diode Conduct	tion) <sup>a</sup>	I <sub>S</sub>	-16	А	
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	-64			
Single Pulse Avalanche Current		I <sub>AS</sub>		-26	
Single Pulse Avalanche Energy		E <sub>AS</sub>	33.8	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	6	62.5	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	20	vv	
Operating Junction and Storage Temperatu	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	*0		
Soldering Recommendations (Peak Temperature) e, f			260	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	81	°C/W		
Junction-to-Case (Drain)		R <sub>thJC</sub>	2.4	0/10		

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).

- e. See solder profile (<u>www.vishav.com/doc?73257</u>). The PowerPAK 1212-8W is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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 For technical questions, contact: <a href="mailto:automostechsupport@vishay.com">automostechsupport@vishay.com</a>

d. Parametric verification ongoing.

www.vishay.com

SQS401ENW Vishay Siliconix

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						1	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = -250 μΑ	-40	-	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2.0	-2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \ge 5 V$	-20	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -12 A	-	0.020	0.029	Ω
Dursing Country On Otata Designations a	Б	$V_{GS} = -10 V$	_	-	0.030	0.043	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	l <sub>D</sub> = -12 A, T <sub>J</sub> = 175 °C	-	0.040	0.051	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -9 A	-	0.035	0.047	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= -15 V, I <sub>D</sub> = -7 A	-	12	-	S
Dynamic <sup>b</sup>					•		<u> </u>
Input Capacitance	C <sub>iss</sub>			-	1565	1875	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V, f = 1 MHz	-	245	295	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	170	205	1
Total Gate Charge <sup>c</sup>	Qg			-	17.7	21.2	
Gate-Source Charge c	Q <sub>gs</sub>	V <sub>GS</sub> = -4.5 V	V <sub>DS</sub> = -20 V, I <sub>D</sub> = -9.3 A	-	5.6	6.6	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	8.1	9.7	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	1.1	1.95	2.8	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	14	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	-20 V, R <sub>L</sub> = 14.2 Ω	-	10	13	1
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ -1.4 A,	$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	36.5	44	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	10.2	13	1
Source-Drain Diode Ratings and Chara	acteristic <sup>b</sup>	•					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-64	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	_	-0.8	-1.1	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

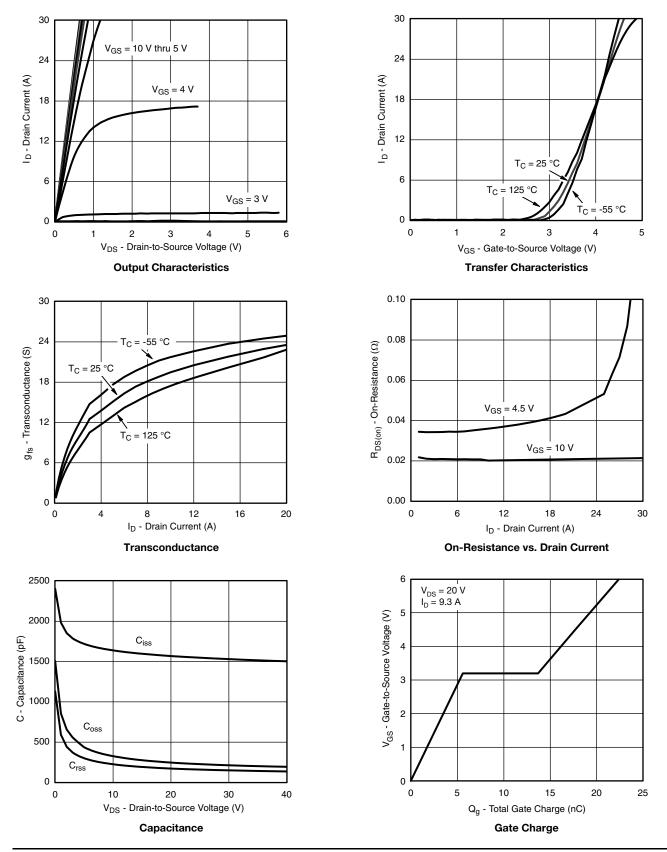
2



SQS401ENW

Vishay Siliconix

### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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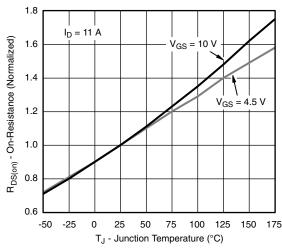
3

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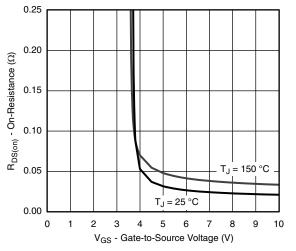
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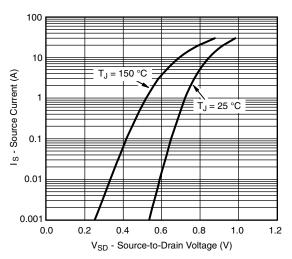
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



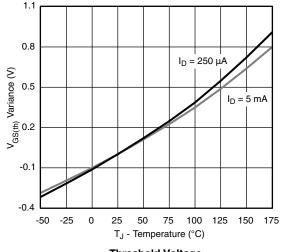
**On-Resistance vs. Junction Temperature** 



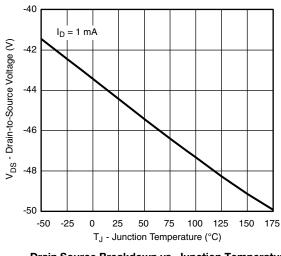
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



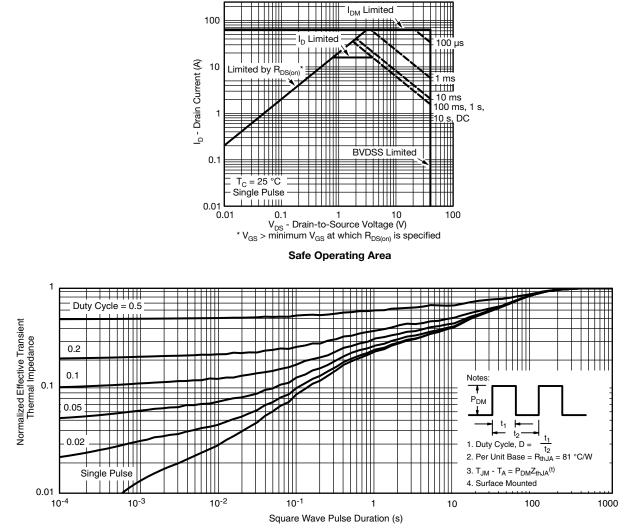




Drain Source Breakdown vs. Junction Temperature



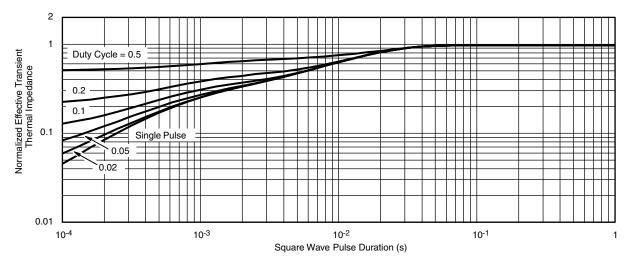
### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?67977">www.vishay.com/ppg?67977</a>.

<sup>•</sup> The characteristics shown in the two graphs



## PowerPAK<sup>®</sup> 1212-8 and PowerPAK 1212-8W

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK 1212-8 and PowerPAK 1212-8W packages:

DATASHEET PART NUMBER	OLD ORDERING CODE <sup>a</sup>	NEW ORDERING CODE	
SQ7414AEN	SQ7414AEN-T1-GE3	SQ7414AEN-T1_GE3	
SQ7414AENW	-	SQ7414AENW-T1_GE3	
SQ7415AEN	SQ7415AEN-T1-GE3	SQ7415AEN-T1_GE3	
SQ7415AENW	-	SQ7415AENW-T1_GE3	
SQS401EN	SQS401EN-T1-GE3	SQS401EN-T1_GE3	
SQS401ENW	-	SQS401ENW-T1_GE3	
SQS405EN	SQS405EN-T1-GE3	SQS405EN-T1_GE3	
SQS405ENW	-	SQS405ENW-T1_GE3	
SQS420EN	SQS420EN-T1-GE3	SQS420EN-T1_GE3	
SQS423EN	SQS423EN-T1-GE3	SQS423EN-T1_GE3	
SQS460EN	SQS460EN-T1-GE3	SQS460EN-T1_GE3	
SQS462EN	SQS462EN-T1-GE3	SQS462EN-T1_GE3	
SQS482EN	SQS482EN-T1-GE3	SQS482EN-T1_GE3	
SQS484EN	34EN SQS484EN-T1-GE3 SQS484EN-T1_G		
SQS490EN	I SQS490EN-T1-GE3 SQS490EN-T1_GE3		
SQS840EN	SQS840EN-T1-GE3	SQS840EN-T1_GE3	
SQS850EN	SQS850EN-T1-GE3	SQS850EN-T1_GE3	

#### Note

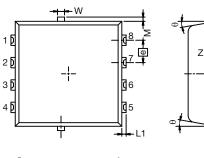
a. Old ordering code is obsolete and no longer valid for new orders

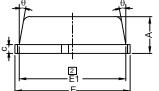


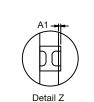
# PowerPAK<sup>®</sup> 1212-8W Case Outline

Δ2

224



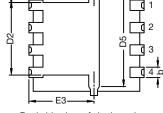




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Б



E2

E4

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Notes
1 Inch will govern

 Dimensions exclusive of mold gate burrs
 Dimensions exclusive of mold flash and cutting burrs

DIM. MILLIMETERS					INCHES	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.97	1.04	1.12	0.038	0.041	0.044
A1	0	-	0.05	0	-	0.002
A2	0	-	0.13	0	-	0.005
b	0.23	0.30	0.41	0.009	0.012	0.016
С	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D4	0.47 typ.			0.0185 typ.		
D5	2.3 typ.			0.090 typ.		
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4		0.34 typ.			0.013 typ.	
е		0.65 BSC.		BSC. 0.026 BSC		
К		0.86 typ.		0.034 typ.		
Н	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
М	0.125 typ.			0.005 typ.		
N: C15-1530-R	ev. B, 16-Nov-15					

Backside view of single pad



Vishay

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